Ordering number : EN8992

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

SS3003CH — Low V_F Schottky Barrier Diode 30V, 3.0A Rectifier

Applications

- High frequency rectification (switching regulators, converters, choppers).

Features

- Small switching noise.
- Low forward voltage (I_F=3A, V_F max=0.42V).
- Ultrasmall package permitting applied sets to be small and slim.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		30	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		30	V
Average Output Current	I_O		3.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	20	A
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=2.0mA	30			V
Forward Voltage	V_F	I_F=2.0A		0.335	0.385	V
		I_F=3.0A		0.37	0.42	V
Reverse Current	I_R	V_R=15V			1.4	mA
Interterminal Capacitance	C	V_R=10V, f=1MHz		90		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=100mA			20	ns
Thermal Resistance	Rth(j-a)	Mouted on a ceramic board (900mm²×0.8mm)		50		°C / W

Marking : SG

SANYO Semiconductor Co., Ltd.

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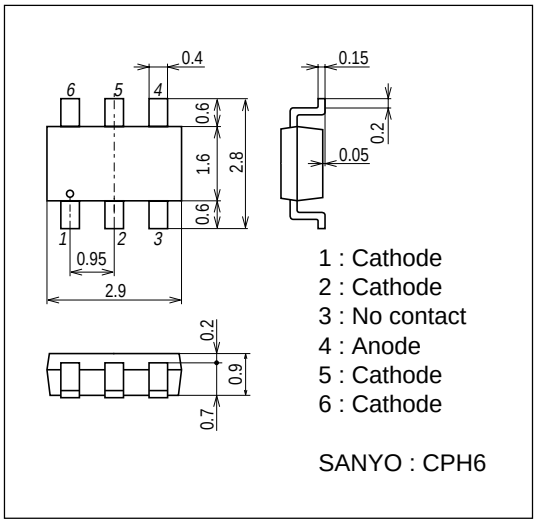
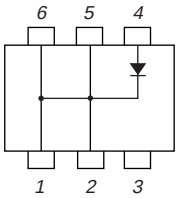
Package Dimensions

unit : mm

7018-012



Electrical Connection



t_{rr} Test Circuit